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TSM500N03

30V N-Channel Power MOSFET

TO-252
(DPAK)



Pin Definition:

1. Gate
2. Drain
3. Source

Key Parameter Performance

Parameter	Value	Unit
V_{DS}	30	V
$R_{DS(on)}$ (max)	$V_{GS} = 10V$	50
	$V_{GS} = 4.5V$	80
Q_g	4	nC

Application

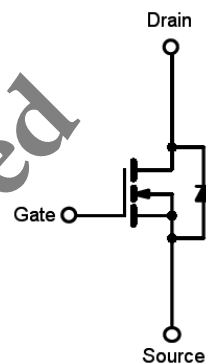
- Portable application
- DC to DC converter

Ordering Information

Part No.	Package	Packing
TSM500N03CP ROG	TO-252	2.5kpcs / 13" Reel

Note: "G" denotes for Halogen- and Antimony-free as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds

Block Diagram



N-Channel MOSFET

Absolute Maximum Ratings ($T_C=25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	I_D	$T_C=25^\circ C$	12.5
		$T_C=100^\circ C$	8
Pulsed Drain Current ^(Note 1)	I_{DM}	40	A
Power Dissipation @ $T_C=25^\circ C$	P_D	12.5	W
Operating Junction Temperature	T_J	150	$^\circ C$
Storage Temperature Range	T_{STG}	-55 to +150	$^\circ C$

Thermal Performance

Parameter	Symbol	Limit	Unit
Thermal Resistance - Junction to Case	$R_{\theta JC}$	10	$^\circ C/W$
Thermal Resistance - Junction to Ambient	$R_{\theta JA}$	110	



Electrical Specifications (T_C=25°C unless otherwise noted)

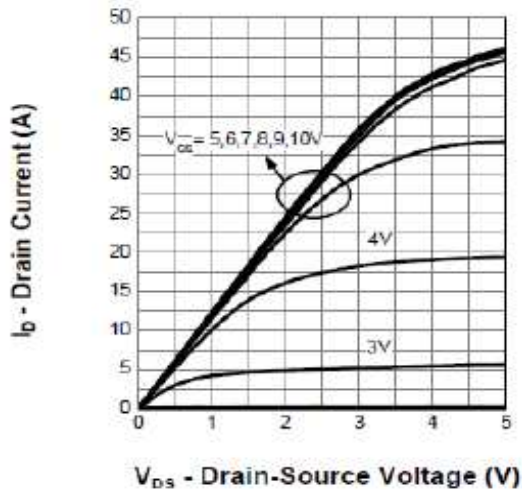
Parameter	Conditions	Symbol	Min	Typ	Max	Unit
Static						
Drain-Source Breakdown Voltage	V _{GS} = 0V, I _D = 250μA	BV _{DSS}	30	--	--	V
Drain-Source On-State Resistance	V _{GS} = 10V, I _D = 8A	R _{DS(ON)}	--	40	50	mΩ
	V _{GS} = 4.5V, I _D = 8A		--	65	80	
Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 250μA	V _{GS(TH)}	1	1.7	3	V
Zero Gate Voltage Drain Current	V _{DS} = 30V, V _{GS} = 0V	I _{DSS}	--	--	1	μA
	V _{DS} = 24V, T _C = 150°C		--	--	25	
Gate Body Leakage	V _{GS} = ±20V, V _{DS} = 0V	I _{GSS}	--	--	±100	nA
Dynamic						
Total Gate Charge ^(Note 2,3)	V _{DS} = 24V, I _D = 10A, V _{GS} = 4.5V	Q _g	--	4	--	nC
Gate-Source Charge ^(Note 2,3)		Q _{gs}	--	1.6	--	
Gate-Drain Charge ^(Note 2,3)		Q _{gd}	--	2.4	--	
Input Capacitance	V _{DS} = 25V, V _{GS} = 0V, f = 1.0MHz	C _{iss}	--	270	--	pF
Output Capacitance		C _{oss}	--	70	--	
Reverse Transfer Capacitance		C _{rss}	--	50	--	
Switching						
Turn-On Delay Time ^(Note 2,3)	V _{DD} = 15V, I _D = 10A, V _{GS} = 10V, R _{GEN} = 3.3Ω	t _{d(on)}	--	7	--	ns
Turn-On Rise Time ^(Note 2,3)		t _r	--	30	--	
Turn-Off Delay Time ^(Note 2,3)		t _{d(off)}	--	10	--	
Turn-Off Fall Time ^(Note 2,3)		t _f	--	3	--	
Source-Drain Diode Ratings and Characteristic						
Diode-Source Forward Voltage	V _{GS} = 0V, I _S = 5A	V _{SD}	--	--	1.3	V
Reverse Recovery Time ^(Note 2)	V _{GS} = 0V, I _S = 10A dI _F /dt = 100A/μs	t _{rr}	--	17	--	ns
Reverse Recovery Charge ^(Note 2)		Q _{rr}	--	10	--	nC

Note:

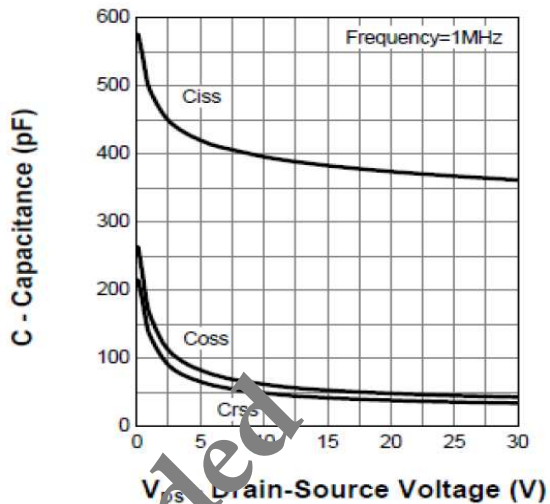
1. Pulse width limited by safe operating area
2. Pulse test: pulse width ≤ 300μs, duty cycle ≤ 2%
3. Switching time is essentially independent of operating temperature.

Electrical Characteristics Curves

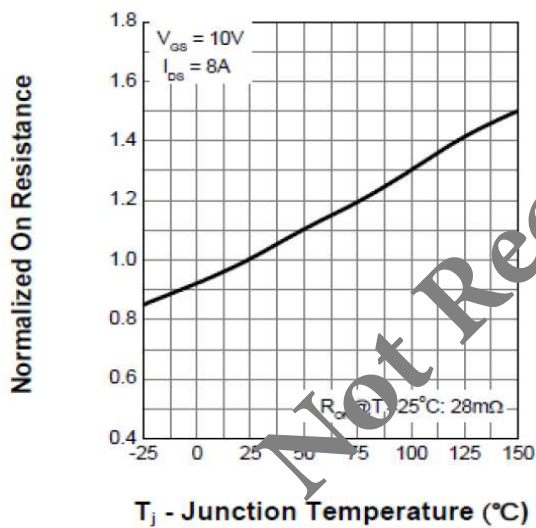
Output Characteristics



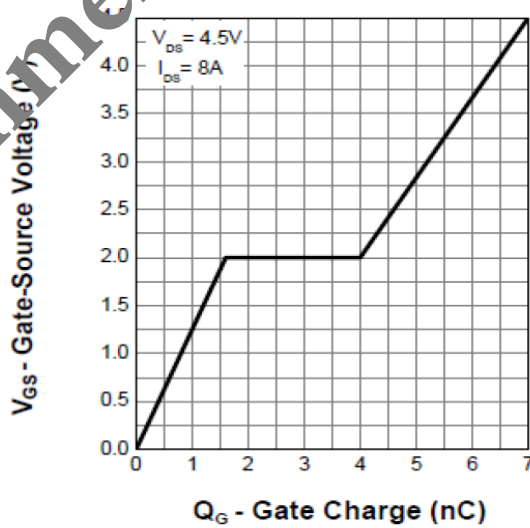
Capacitance



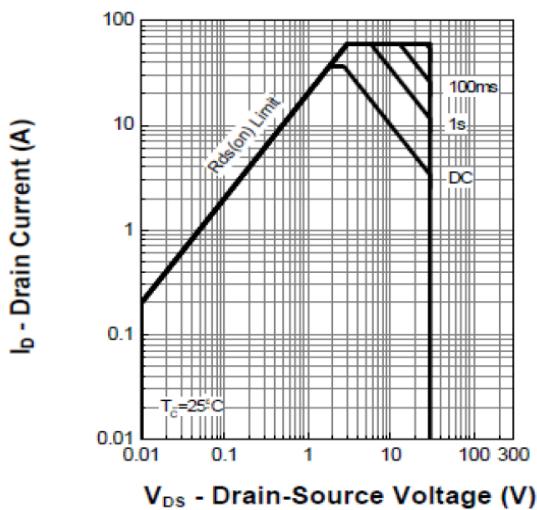
Drain-Source On-Resistance



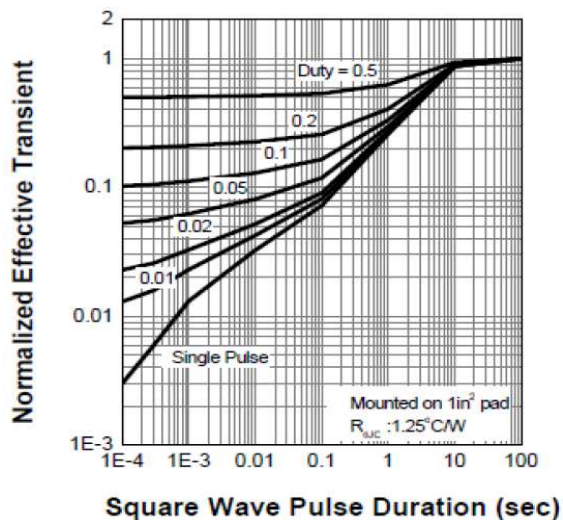
Gate-Source Voltage vs. Gate Charge



Safe Operation Area

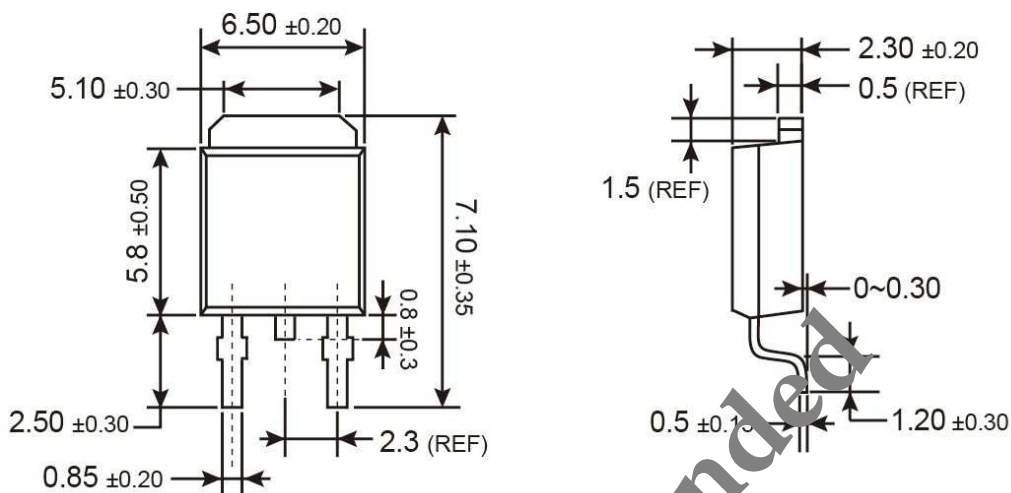


Thermal Transient Impedance



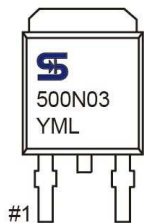


TO-252 Mechanical Drawing



Unit: Millimeters

Marking Diagram



- Y** = Year Code
- M** = Month Code for Halogen Free Product
(**Q**=Jan, **V**=Feb, **Q**=Mar, **R**=Apr, **S**=May, **T**=Jun, **U**=Jul, **V**=Aug, **W**=Sep, **X**=Oct, **Y**=Nov, **Z**=Dec)
- L** = Lot Code

Not Recommended

Not Recommended

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